



**III SEMESTER B.Tech (BME) DEGREE END SEM EXAMINATIONS NOVEMBER 2017**  
**SUBJECT: ANALOG ELECTRONICS (BME 2102)**  
**(REVISED CREDIT SYSTEM)**

**Nov 16<sup>th</sup> Thursday, 2017, 9 AM to 12 NOON**

**TIME: 3 HOURS**

**MAX. MARKS: 100**

**Instructions to Candidates:**

- 1. Answer FIVE full questions.**
- 2. Draw labeled diagram wherever necessary**

1. (a) Assume a Si transistor with  $\beta = 50$ ,  $V_{BE} = 0.6\text{V}$ ,  $V_{CC} = 22.5\text{V}$ ,  $R_C = 5.6\text{K}$ . It is desired to establish a quiescent point at  $V_{CE} = 12\text{V}$ ,  $I_C = 1.5\text{mA}$  &  $S \leq 3$ . Find  $R_E$ ,  $R_1$  &  $R_2$ . 8
- (b) Derive an expression for the factor that describes the stabilization of collector current against variations in the value of  $I_{CO}$ , keeping the values of  $V_{BE}$  and  $\beta$  constant. 6
- (c) For a collector to base bias circuit with emitter resistance, show that  $S = \frac{1 + \beta}{1 + \beta \frac{(R_C + R_e)}{(R_C + R_e + R)}}$ .  $R$  is the resistance connected between collector and base of the transistor. 6
2. (a) A two stage RC coupled amplifier has the following parameters.  $h_{fe} = 50$ ,  $h_{ie} = 1.1\text{K}$ ,  $R_C = 3\text{K}$ ,  $C_e = 50\text{pF}$ ,  $R_1 = 50\text{K}$ ,  $R_2 = 50\text{K}$  &  $R_e = 2\text{K}$  for each stage.
  - i) What must be the value of  $C_b$  in order that the frequency characteristic of each stage be flat within 1 dB down to 10 Hz. 8
  - ii) Repeat part i) if the overall gain of both stages is to be down 1 dB at 10 Hz.
  - iii) What is the overall mid band voltage gain?

- (b) Express  $h_{re}$  &  $h_{fe}$  in terms of common collector  $h$  – parameters. Graphically determine both the  $h$ -parameters. 6
- (c) Derive expressions for the overall lower 3 dB frequency and overall upper 3 dB frequency of non-interactive cascaded amplifier. 6
3. (a) i) A transistor amplifier with un bypassed  $R_e$  is having an overall trans conductance gain of  $-1mA/v$ , overall voltage gain of  $-4$  &  $D = 50$ . If find  $R_e, R_L$  &  $R_{if}$ . 4+4
- ii) Draw the approximate small signal model for the common collector transistor amplifier configuration, and determine the expressions for: voltage gain, current gain, input resistance and output resistance.
- (b) Analyze a FET source follower circuit to determine the voltage gain with feedback, input resistance with feedback and output resistance with feedback. 6
- (c) Design a current series feedback amplifier circuit with the following specifications: Input resistance with feedback 50 K $\Omega$ . The following specifications are provided: BC107,  $h_{fe} = 200, h_{ie} = 1K, V_{CE} = 5v$  &  $I_C = 2mA$ . 6
4. (a) Draw the model that describes the transistor at high frequencies and determine the expressions for its conductance's. 8
- (b) Show that  $Z_i = \frac{1 - 5\alpha^2 - j(6\alpha - \alpha^3)}{3 - \alpha^2 - j4\alpha}$  of the feedback network of FET RC-phase shift oscillator and at the frequency of oscillation  $\alpha = \sqrt{6}$  input impedance of the feedback network is  $(0.83 - j2.7)R$  6
- (c) Design a suitable oscillator circuit that generates oscillations having a frequency of 500 KHz. The stability factor is 6. The specifications provided are: BC107,  $V_{CEQ} = 5v, I_{CQ} = 2mA, h_{fe} = 300$  &  $h_{ie} = 2.2K$ . 6

5. (a) i) For a large signal class A power amplifier circuit, calculate input power, output power and efficiency for an input voltage resulting in a base current of 20 mA peak. Determine the power dissipated by the transistor. The specifications provided are:  $R_B = 1K, R_L = 30\Omega, \beta = 25$  &  $V_{CC} = 20V$ . 5+3
- ii) To deliver 10 watts from a class B push pull amplifier the collector dissipation maximum power is 4 watts or transistors have to be selected that have collector dissipation of approximately 2 watts each. Mathematically derive the relation between maximum collector power dissipation and maximum output power,
- (b) Analyze a common source amplifier circuit with bypass capacitor to obtain expressions for its voltage gain and current gain. What is the effect of source resistance on its voltage gain? 6
- (c) i) How different is enhancement MOSFET with respect to depletion MOSFET taking into consideration their output and transfer characteristics? Explain. 4+2
- ii) Highlight important features of large signal class AB power amplifier.